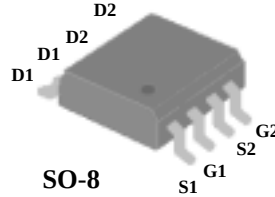


N AND P-CHANNEL ENHANCEMENT MODE POWER MOSFET

PRODUCT SUMMARY

Simple Drive Requirement
Low On-resistance
Fast Switching

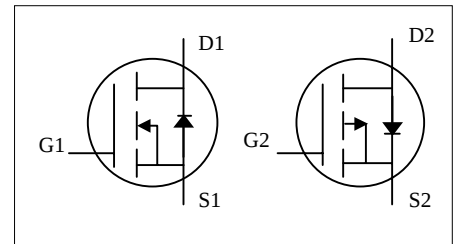


N-CH	BV_{DSS}	20V
	$R_{DS(ON)}$	30m Ω
	I_D	6A
P-CH	BV_{DSS}	-20V
	$R_{DS(ON)}$	50m Ω
	I_D	-5A

DESCRIPTION

The advanced power MOSFETs from Silicon Standard Corp. provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Pb-free; RoHS-compliant

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	± 12	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current ³	6	-5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current ³	4.8	-4	A
I_{DM}	Pulsed Drain Current ¹	20	-20	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2.0		W
	Linear Derating Factor	0.016		W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150		$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150		$^\circ C$

THERMAL DATA

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³ Max.	62.5	$^\circ C/W$

N-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.037	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =6A	-	-	30	mΩ
		V _{GS} =2.5V, I _D =5.2A	-	-	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.5	-	1.2	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =6A	-	18.5	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =20V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =16V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±12V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =6A	-	9	15	nC
Q _{gs}	Gate-Source Charge	V _{DS} =10V	-	1.8	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	4.2	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =10V	-	29	-	ns
t _r	Rise Time	I _D =1A	-	65	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =6Ω, V _{GS} =4.5V	-	60	-	ns
t _f	Fall Time	R _D =10Ω	-	50	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	300	480	pF
C _{oss}	Output Capacitance	V _{DS} =8V	-	255	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	115	-	pF

SOURCE-DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1.7A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =6A, V _{GS} =0V,	-	26	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	17	-	nC

P-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

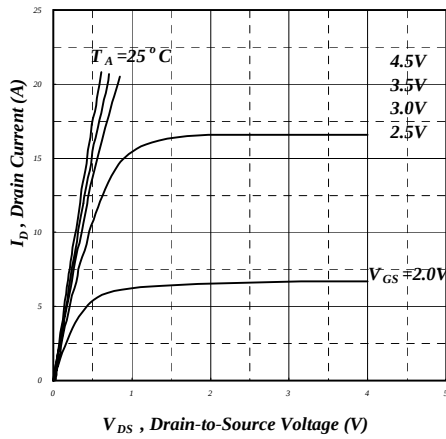
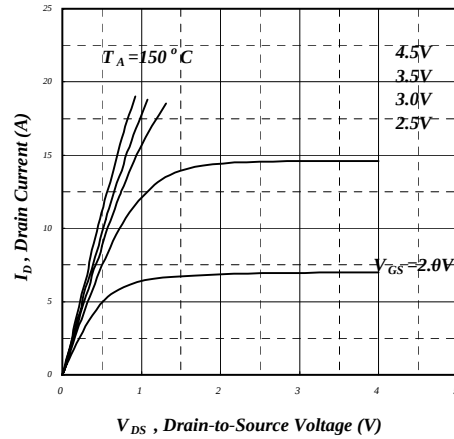
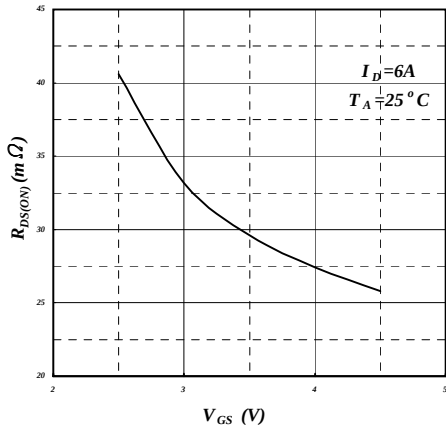
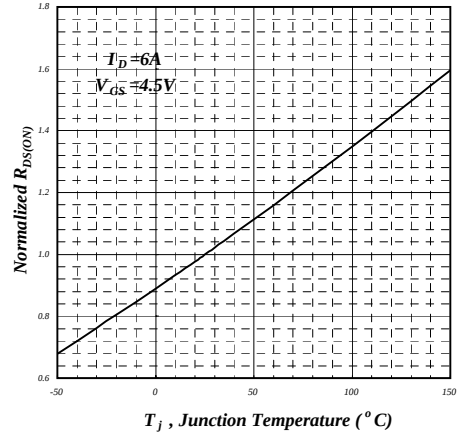
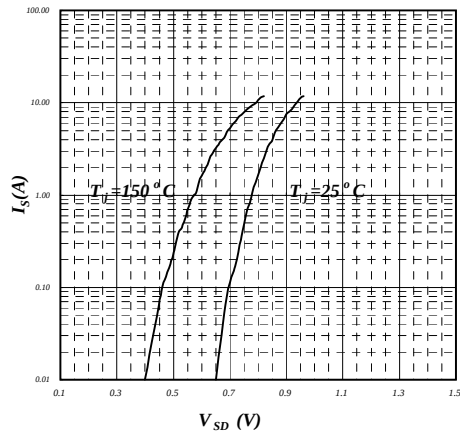
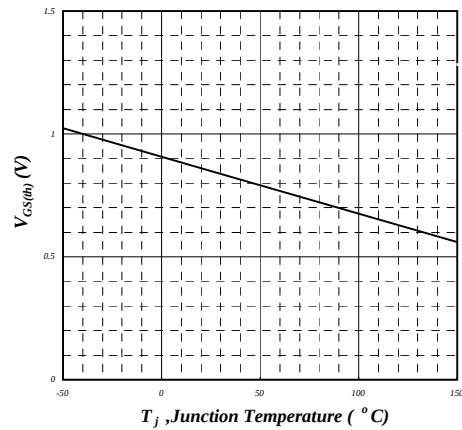
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	-20	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =-1mA	-	-0.037	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-2.2A	-	-	50	mΩ
		V _{GS} =-2.5V, I _D =-1.8A	-	-	90	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-0.5	-	-1	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-2.2A	-	2.5	-	S
I _{DSS}	Drain-Source Leakage Current (T=25°C)	V _{DS} =-20V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T=70°C)	V _{DS} =-16V, V _{GS} =0V	-	-	-25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±12V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-5A	-	14	20	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-16V	-	2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	5.6	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-10V	-	10	-	ns
t _r	Rise Time	I _D =-2.2A	-	11	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =6Ω, V _{GS} =-10V	-	58	-	ns
t _f	Fall Time	R _D =4.5Ω	-	38	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	940	1500	pF
C _{oss}	Output Capacitance	V _{DS} =-20V	-	400	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	160	-	pF

SOURCE-DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.8A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-2.2A, V _{GS} =0V,	-	25	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	21	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in² copper pad of FR4 board ; 135°C/W when mounted on Min. copper pad.

N-Channel

Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. On-Resistance v.s. Gate Voltage

**Fig 4. Normalized On-Resistance
v.s. Junction Temperature**

**Fig 5. Forward Characteristic of
Reverse Diode**

**Fig 6. Gate Threshold Voltage v.s.
Junction Temperature**

N-Channel

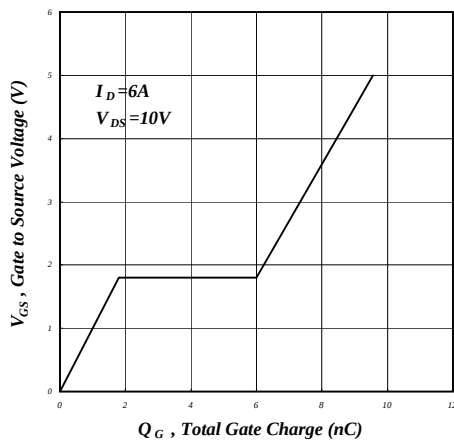


Fig 7. Gate Charge Characteristics

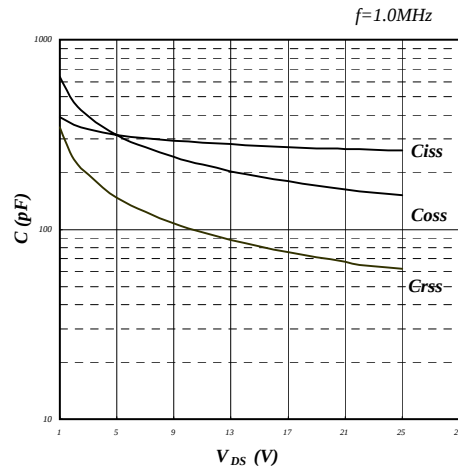


Fig 8. Typical Capacitance Characteristics

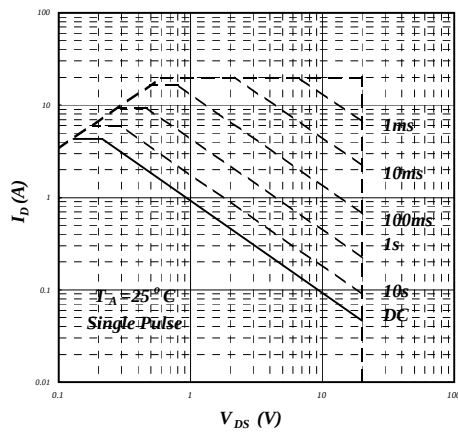


Fig9. Maximum Safe Operating Area

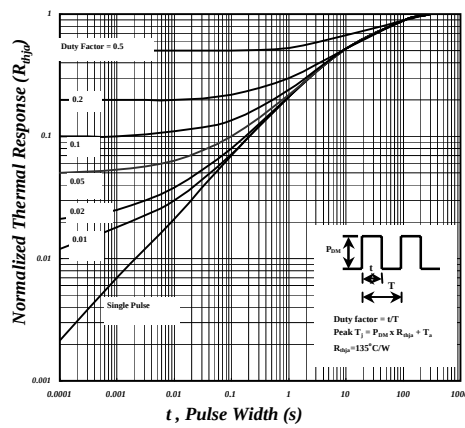


Fig 10. Effective Transient Thermal Impedance

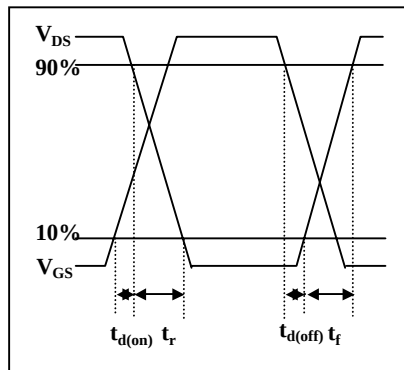


Fig 11. Switching Time Waveform

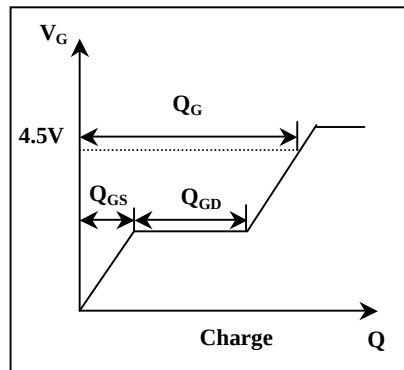


Fig 12. Gate Charge Waveform

P-Channel

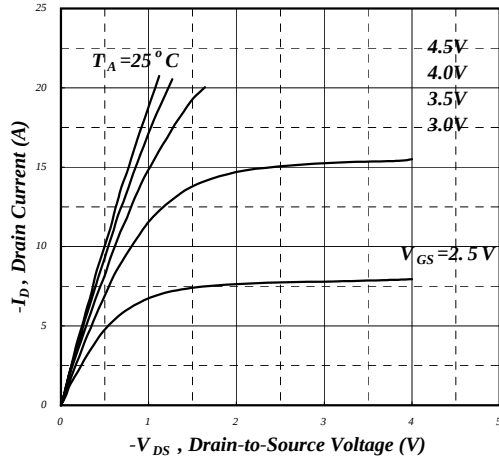


Fig 1. Typical Output Characteristics

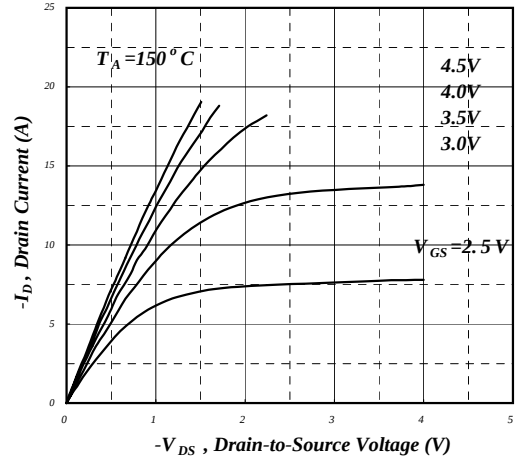


Fig 2. Typical Output Characteristics

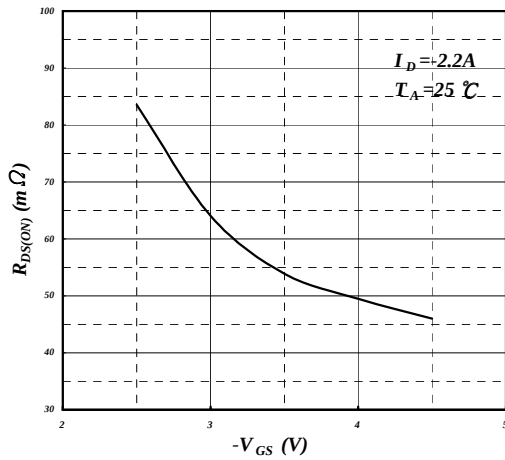


Fig 3. On-Resistance v.s. Gate Voltage

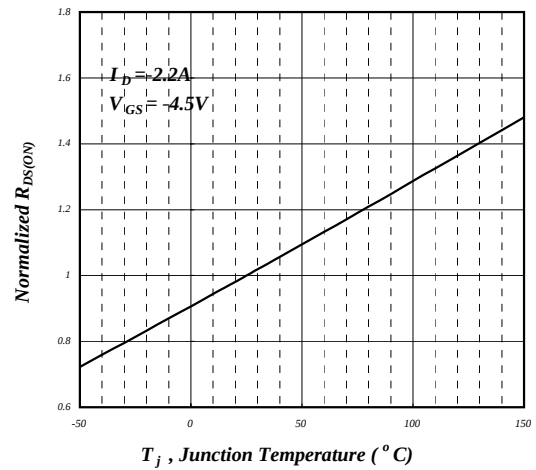


Fig 4. Normalized On-Resistance v.s. Junction Temperature

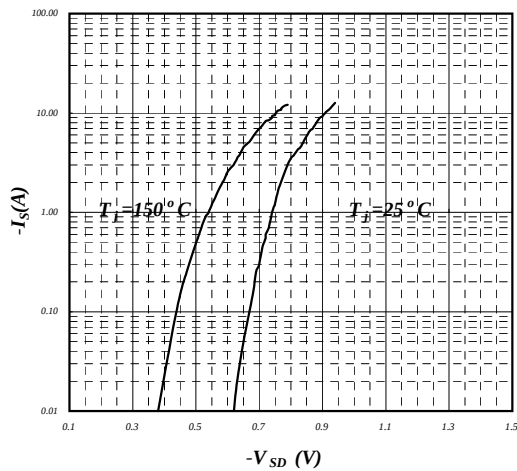


Fig 5. Forward Characteristic of Reverse Diode

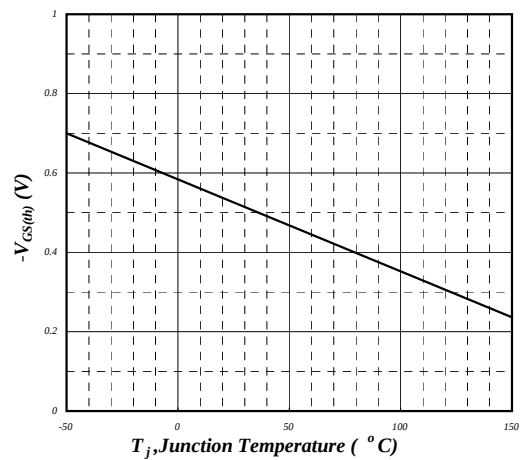
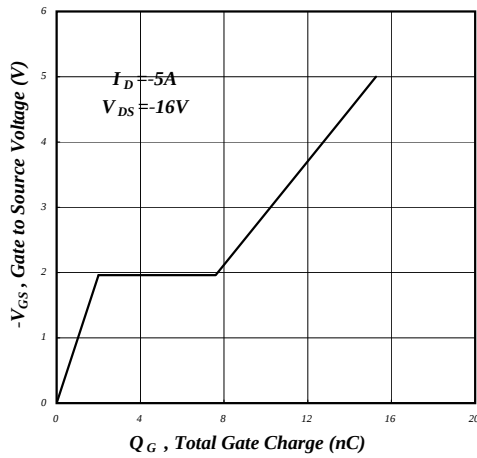
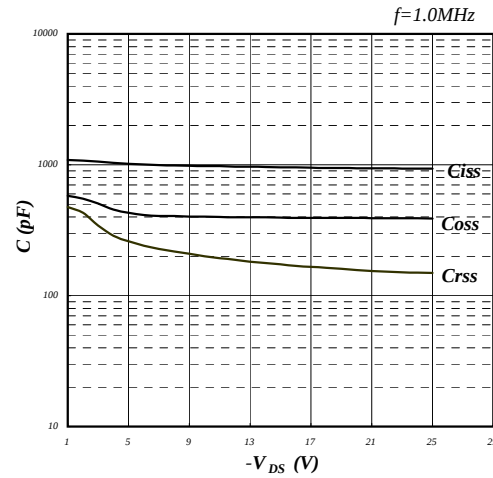
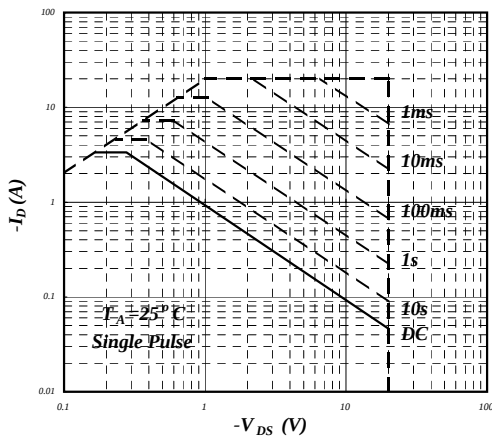
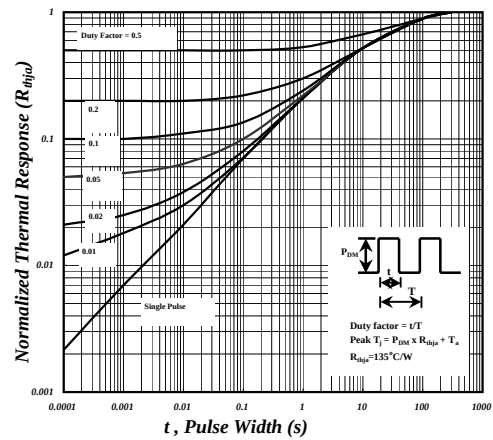
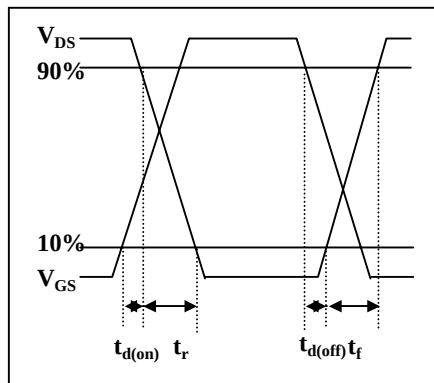
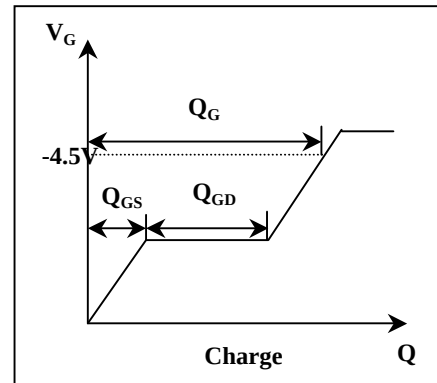


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

P-Channel

Fig 7. Gate Charge Characteristics

Fig 8. Typical Capacitance Characteristics

Fig 9. Maximum Safe Operating Area

Fig 10. Effective Transient Thermal Impedance

Fig 11. Switching Time Waveform

Fig 12. Gate Charge Waveform

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